

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-20V	0.65Ω@-4.5V	-0.66A
	0.85Ω@-2.5V	

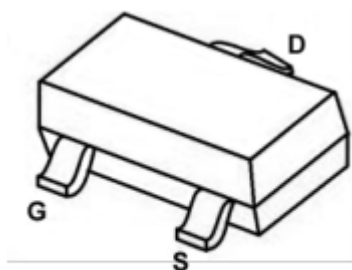
Feature

- Surface Mount Package
- P-Channel Switch with Low $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive
- ESD Protected: 2KV

Applications

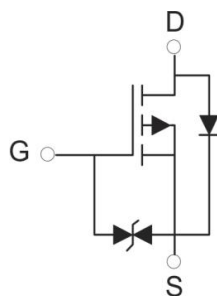
- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics

Package

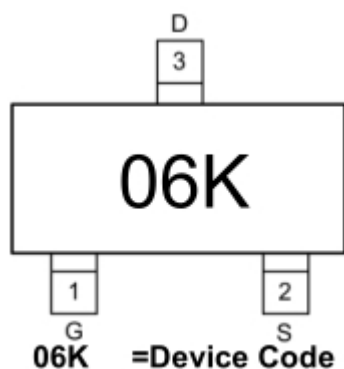


SOT-523

Circuit diagram



Marking



Absolute maximum ratings

($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	-0.66	A
Pulsed Drain Current	I_{DM}	-1.2	A
Power Dissipation	P_D	0.15	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	$T_{STG.}$	-55~ +150	$^{\circ}\text{C}$

Electrical characteristics

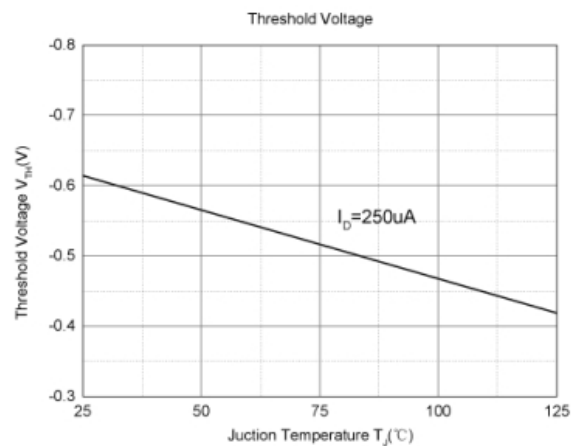
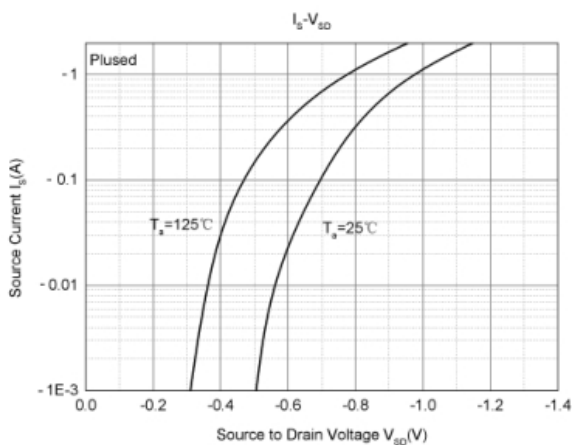
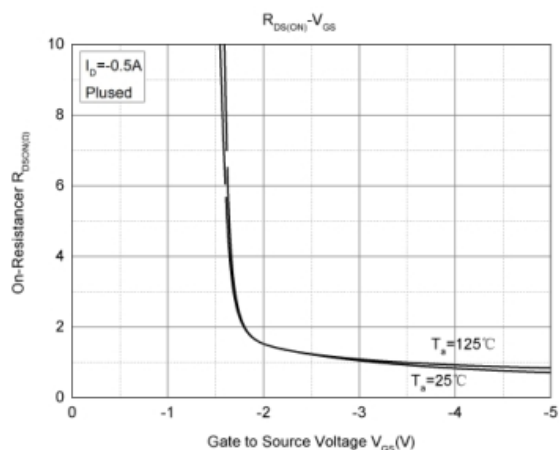
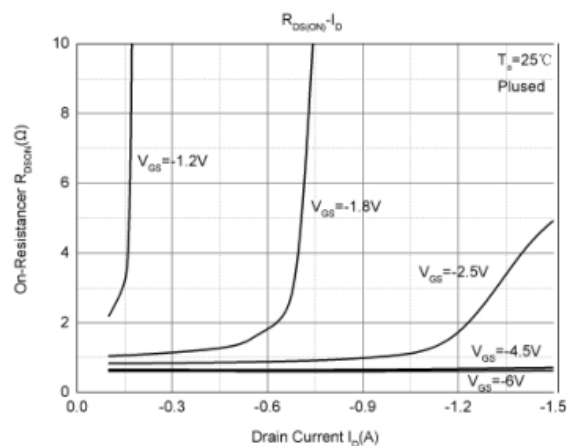
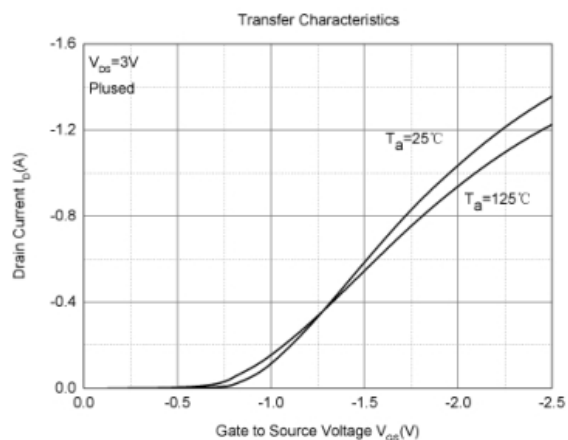
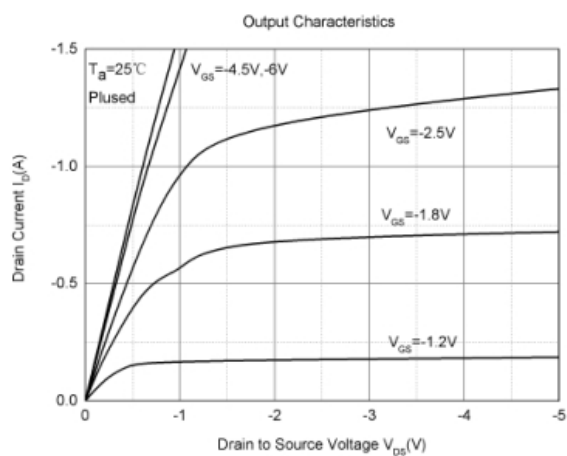
($T_A = 25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	BV (BR)DSS	V _{GS} = 0V, I _D = -250μA	-20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = -16V, V _{GS} = 0V			-1	uA
Gate-body leakage current	I _{GSS}	V _{GS} = ±10V, V _{DS} = 0V			±10	uA
Gate threshold voltage ⁽¹⁾	V _{GS(th)}	V _{DS} =V _{GS} , I _D = -250μA	-0.35	-0.65	-1	V
Drain-source on-resistance ⁽¹⁾	R _{DS(on)}	V _{GS} = -4.5V, I _D = -0.5A		0.65	0.75	Ω
		V _{GS} = -2.5V, I _D = -0.2A		0.85	1.0	
Dynamic Characteristics						
Input capacitance	C _{iss}	V _{DS} = -16V, V _{GS} =0V, f=1MHz		113		pF
Output capacitance	C _{oss}			15		
Reverse transfer capacitance	C _{rss}			9		
Turn-on Delay Time	T _{d(on)}	V _{DS} = -10V, I _D =200mA , V _{GS} = -4.5V, R _{GEN} =10Ω		9		nS
Turn-on Rise Time	T _r			5.7		
Turn-Off Delay Time	T _{d(off)}			32.6		
Turn-Off Fall Time	t _f			20.3		
Source-Drain Diode Characteristics						
Diode Forward voltage	V _{SD}	I _S =-0.5A, V _{GS} = 0V			-1.2	V

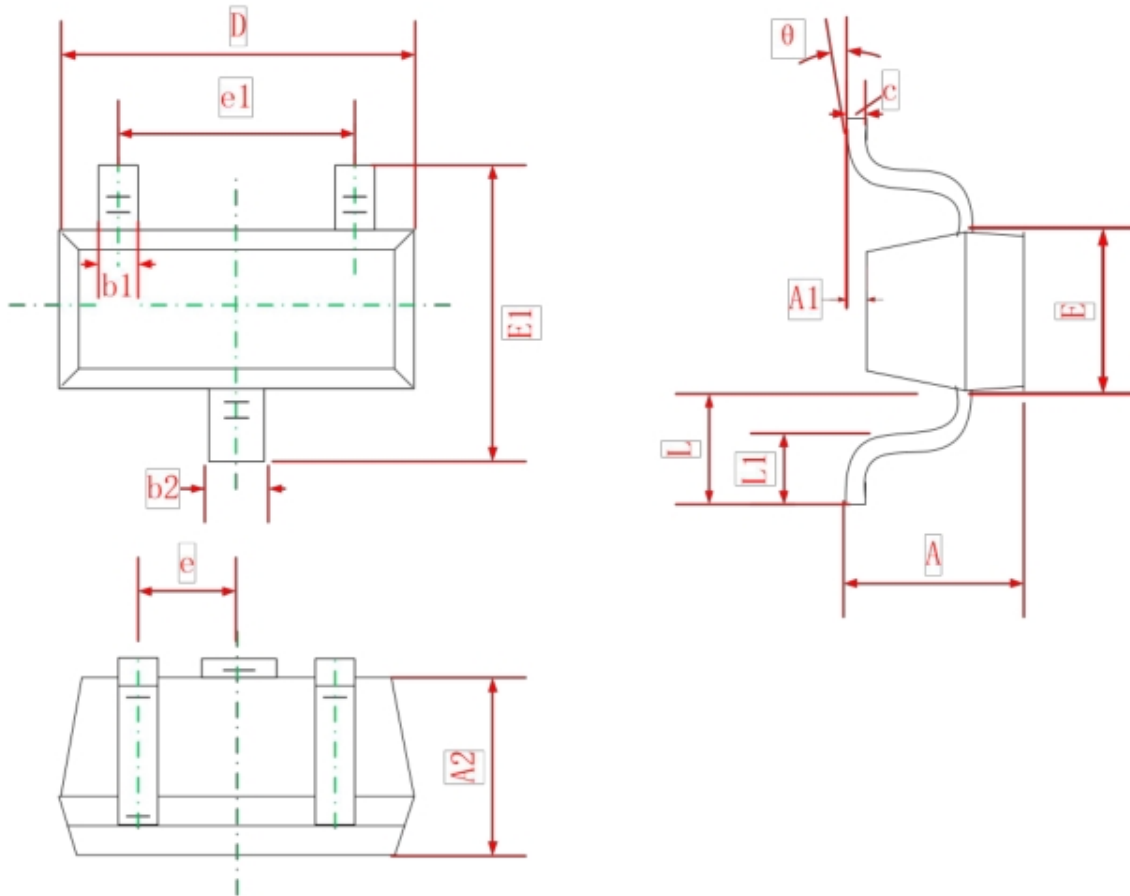
Notes:

1. Pulse Test: Pulse Width < 300 μs , Duty Cycle $\leq 2\%$.
2. Guaranteed by design, not subject to production testing.

Typical Characteristics



SOT-523 Package Information



Symbol	Dimensions In Millimeters	
	Min	Max
A	0.700	0.900
A1	0.000	0.100
A2	0.700	0.800
b1	0.150	0.250
b2	0.250	0.350
C	0.100	0.200
D	1.500	1.700
E	0.700	0.900
E1	1.450	1.750
e	0.500 TYP	
e1	0.900	1.100
L	0.400 REF	
L1	0.260	0.460
θ	0°	8°